

MOSFET

Metal Oxide Semiconductor Field Effect Transistor

CoolMOS™ C7

650V CoolMOS™ C7 Power Transistor
IPW65R045C7

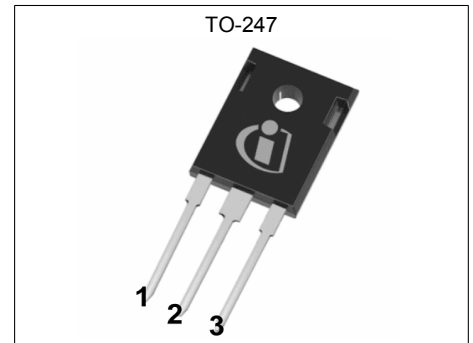
Data Sheet

Rev. 2.1
Final

1 Description

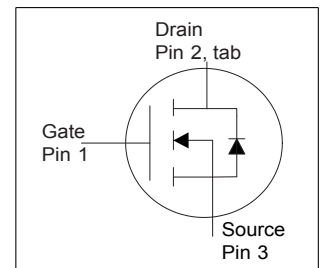
CoolMOS™ is a revolutionary technology for high voltage power MOSFETs, designed according to the superjunction (SJ) principle and pioneered by Infineon Technologies.

CoolMOS™ C7 series combines the experience of the leading SJ MOSFET supplier with high class innovation. The product portfolio provides all benefits of fast switching superjunction MOSFETs offering better efficiency, reduced gate charge, easy implementation and outstanding reliability.



Features

- Increased MOSFET dv/dt ruggedness
- Better efficiency due to best in class FOM $R_{DS(on)} \cdot E_{oss}$ and $R_{DS(on)} \cdot Q_g$
- Best in class $R_{DS(on)}$ /package
- Easy to use/drive
- Pb-free plating, halogen free mold compound
- Qualified for industrial grade applications according to JEDEC (J-STD20 and JESD22)



Benefits

- Enabling higher system efficiency
- Enabling higher frequency / increased power density solutions
- System cost / size savings due to reduced cooling requirements
- Higher system reliability due to lower operating temperatures



Applications

PFC stages and hard switching PWM stages for e.g. Computing, Server, Telecom, UPS and Solar.



Please note: For MOSFET paralleling the use of ferrite beads on the gate or separate totem poles is generally recommended.

Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	700	V
$R_{DS(on),max}$	45	mΩ
$Q_{g,typ}$	93	nC
$I_{D,pulse}$	212	A
$E_{oss}@400V$	11.7	μJ
Body diode di/dt	60	A/μs

Type / Ordering Code	Package	Marking	Related Links
IPW65R045C7	PG-TO 247	65C7045	see Appendix A

Table of Contents

Description	2
Maximum ratings	4
Thermal characteristics	5
Electrical characteristics	6
Electrical characteristics diagrams	8
Test Circuits	12
Package Outlines	13
Appendix A	14
Revision History	15
Disclaimer	15

2 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D	-	-	46 29	A	$T_C=25^\circ\text{C}$ $T_C=100^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	212	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	249	mJ	$I_D=12\text{A}; V_{DD}=50\text{V}$
Avalanche energy, repetitive	E_{AR}	-	-	1.25	mJ	$I_D=12\text{A}; V_{DD}=50\text{V}$
Avalanche current, single pulse	I_{AS}	-	-	12.0	A	-
MOSFET dv/dt ruggedness	dv/dt	-	-	100	V/ns	$V_{DS}=0\dots400\text{V}$
Gate source voltage (static)	V_{GS}	-20	-	20	V	static;
Gate source voltage (dynamic)	V_{GS}	-30	-	30	V	AC (f>1 Hz)
Power dissipation	P_{tot}	-	-	227	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	-
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	-
Mounting torque	-	-	-	60	Ncm	M3 and M3.5 screws
Continuous diode forward current	I_S	-	-	46	A	$T_C=25^\circ\text{C}$
Diode pulse current ²⁾	$I_{S,pulse}$	-	-	212	A	$T_C=25^\circ\text{C}$
Reverse diode dv/dt ³⁾	dv/dt	-	-	1.5	V/ns	$V_{DS}=0\dots400\text{V}, I_{SD}\leq I_S, T_j=25^\circ\text{C}$
Maximum diode commutation speed	di/dt	-	-	60	A/ μs	$V_{DS}=0\dots400\text{V}, I_{SD}\leq I_S, T_j=25^\circ\text{C}$
Insulation withstand voltage	V_{ISO}	-	-	n.a.	V	$V_{rms}, T_C=25^\circ\text{C}, t=1\text{min}$

¹⁾ Limited by $T_{j,max}$.

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

3 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	0.55	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	leaded
Thermal resistance, junction - ambient for SMD version	R_{thJA}	-	-	-	°C/W	n.a.
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	-	-	260	°C	1.6mm (0.063 in.) from case for 10s

4 Electrical characteristics

at $T_j=25^\circ\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	650	-	-	V	$V_{GS}=0\text{V}$, $I_D=1\text{mA}$
Gate threshold voltage	$V_{(GS)th}$	3	3.5	4	V	$V_{DS}=V_{GS}$, $I_D=1.25\text{mA}$
Zero gate voltage drain current	I_{DSS}	-	-	2	μA	$V_{DS}=650$, $V_{GS}=0\text{V}$, $T_j=25^\circ\text{C}$ $V_{DS}=650$, $V_{GS}=0\text{V}$, $T_j=150^\circ\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=20\text{V}$, $V_{DS}=0\text{V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	0.040 0.096	0.045 -	Ω	$V_{GS}=10\text{V}$, $I_D=24.9\text{A}$, $T_j=25^\circ\text{C}$ $V_{GS}=10\text{V}$, $I_D=24.9\text{A}$, $T_j=150^\circ\text{C}$
Gate resistance	R_G	-	0.85	-	Ω	$f=1\text{MHz}$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	4340	-	pF	$V_{GS}=0\text{V}$, $V_{DS}=400\text{V}$, $f=250\text{kHz}$
Output capacitance	C_{oss}	-	70	-	pF	$V_{GS}=0\text{V}$, $V_{DS}=400\text{V}$, $f=250\text{kHz}$
Effective output capacitance, energy related ¹⁾	$C_{o(er)}$	-	146	-	pF	$V_{GS}=0\text{V}$, $V_{DS}=0\dots400\text{V}$
Effective output capacitance, time related ²⁾	$C_{o(tr)}$	-	1630	-	pF	$I_D=\text{constant}$, $V_{GS}=0\text{V}$, $V_{DS}=0\dots400\text{V}$
Turn-on delay time	$t_{d(on)}$	-	20	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=24.9\text{A}$, $R_G=3.3\Omega$
Rise time	t_r	-	14	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=24.9\text{A}$, $R_G=3.3\Omega$
Turn-off delay time	$t_{d(off)}$	-	82	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=24.9\text{A}$, $R_G=3.3\Omega$
Fall time	t_f	-	7	-	ns	$V_{DD}=400\text{V}$, $V_{GS}=13\text{V}$, $I_D=24.9\text{A}$, $R_G=3.3\Omega$

Table 6 Gate charge characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	23	-	nC	$V_{DD}=400\text{V}$, $I_D=24.9\text{A}$, $V_{GS}=0$ to 10V
Gate to drain charge	Q_{gd}	-	30	-	nC	$V_{DD}=400\text{V}$, $I_D=24.9\text{A}$, $V_{GS}=0$ to 10V
Gate charge total	Q_g	-	93	-	nC	$V_{DD}=400\text{V}$, $I_D=24.9\text{A}$, $V_{GS}=0$ to 10V
Gate plateau voltage	V_{plateau}	-	5.4	-	V	$V_{DD}=400\text{V}$, $I_D=24.9\text{A}$, $V_{GS}=0$ to 10V

¹⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 400V

²⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 400V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.9	-	V	$V_{GS}=0V, I_F=24.9A, T_j=25^{\circ}C$
Reverse recovery time	t_{rr}	-	725	-	ns	$V_R=400V, I_F=46A, di_F/dt=60A/\mu s$
Reverse recovery charge	Q_{rr}	-	13	-	μC	$V_R=400V, I_F=46A, di_F/dt=60A/\mu s$
Peak reverse recovery current	I_{rrm}	-	36	-	A	$V_R=400V, I_F=46A, di_F/dt=60A/\mu s$

5 Electrical characteristics diagrams

Table 8

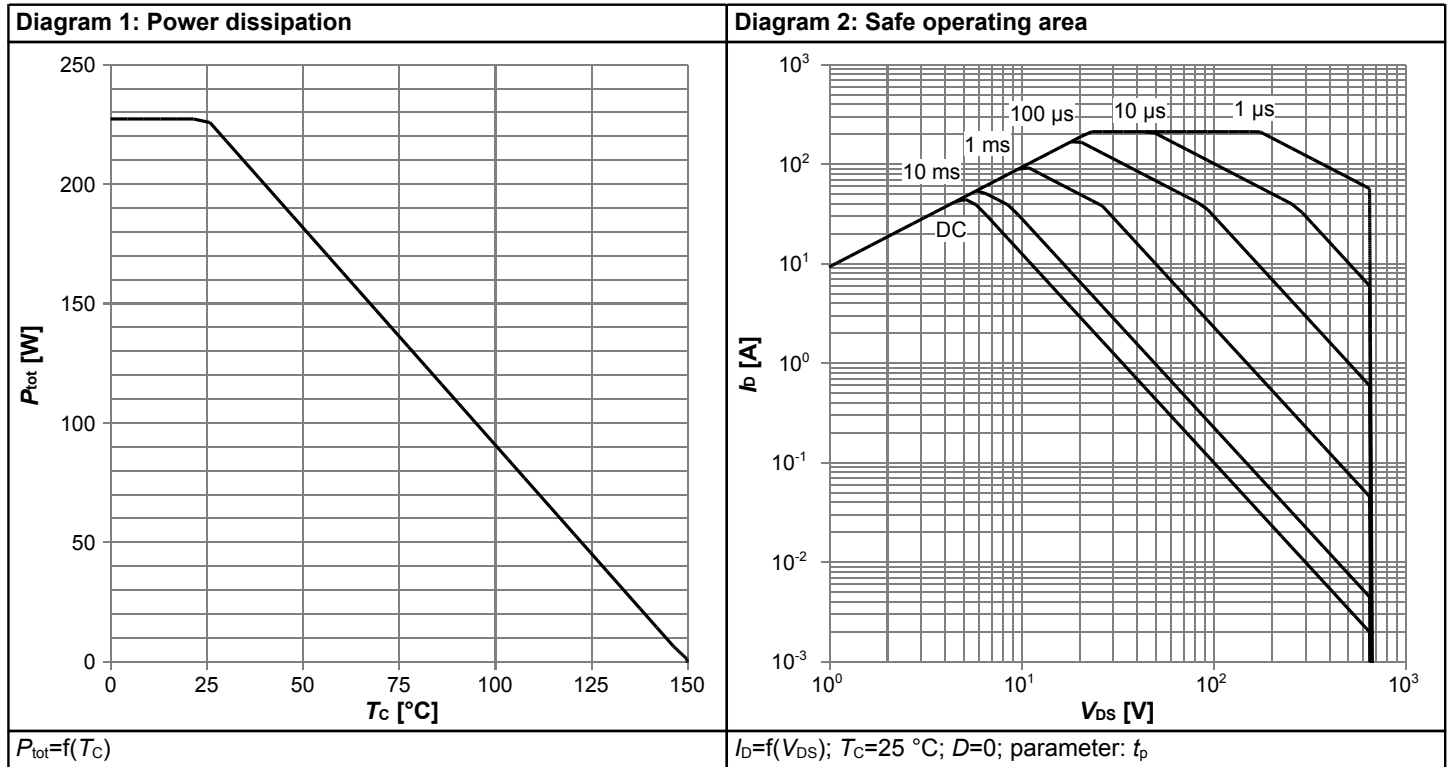


Table 9

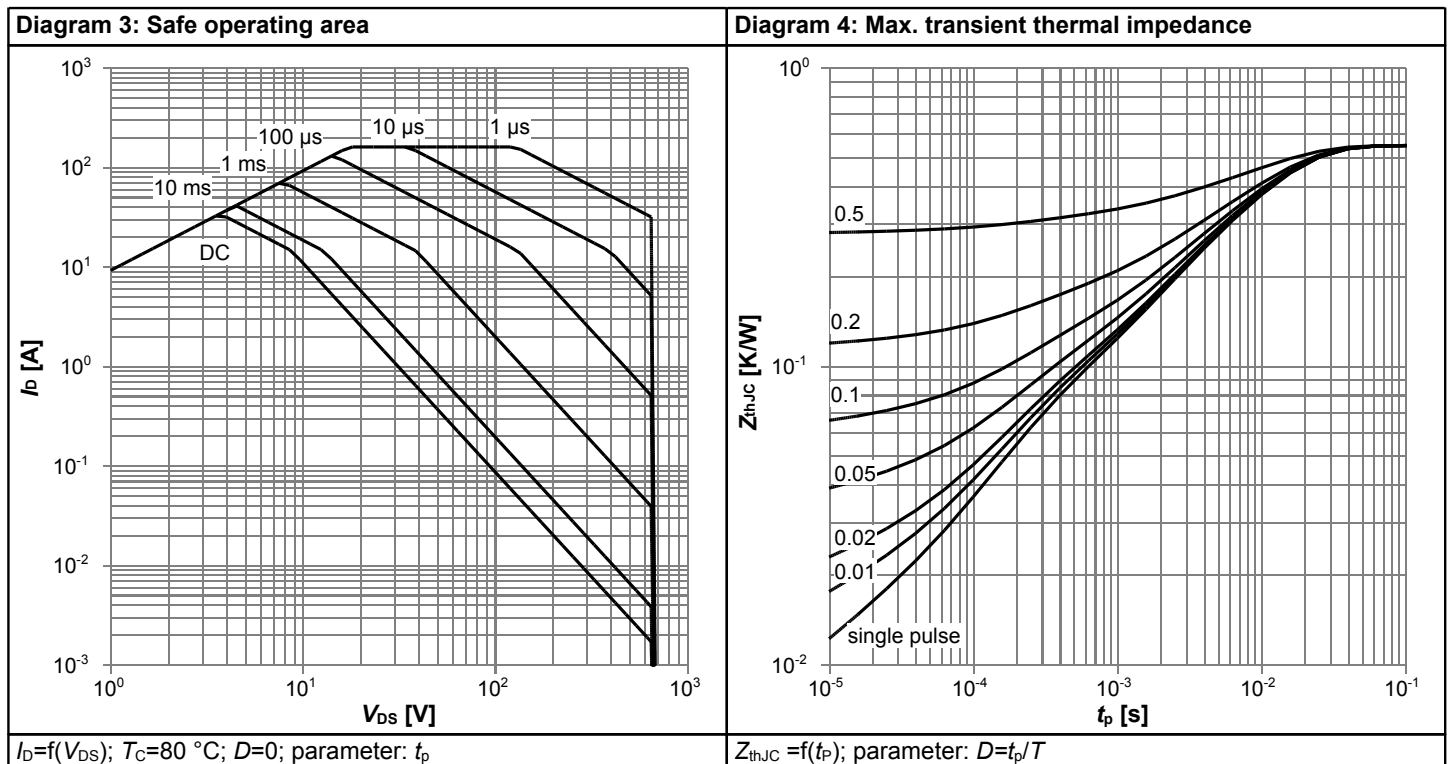


Table 10

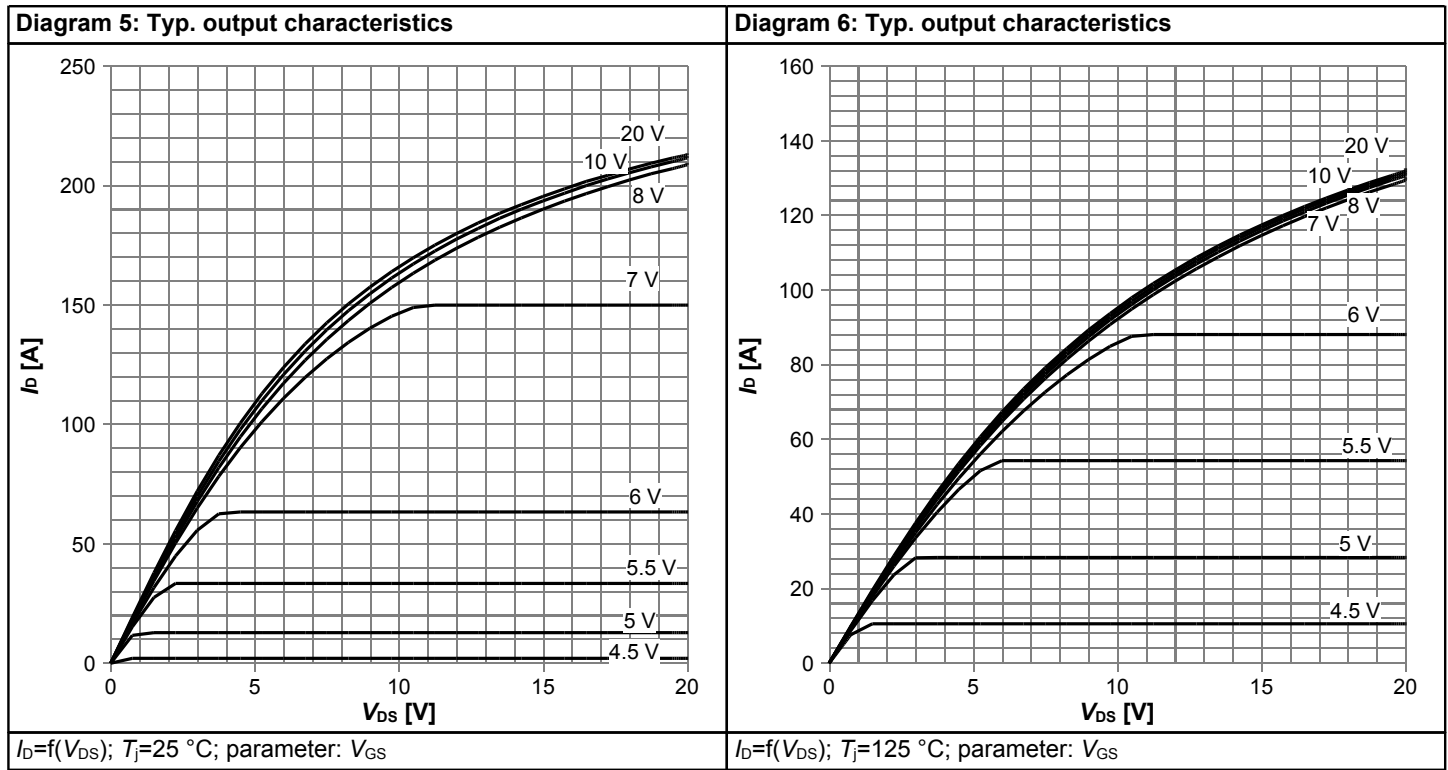


Table 11

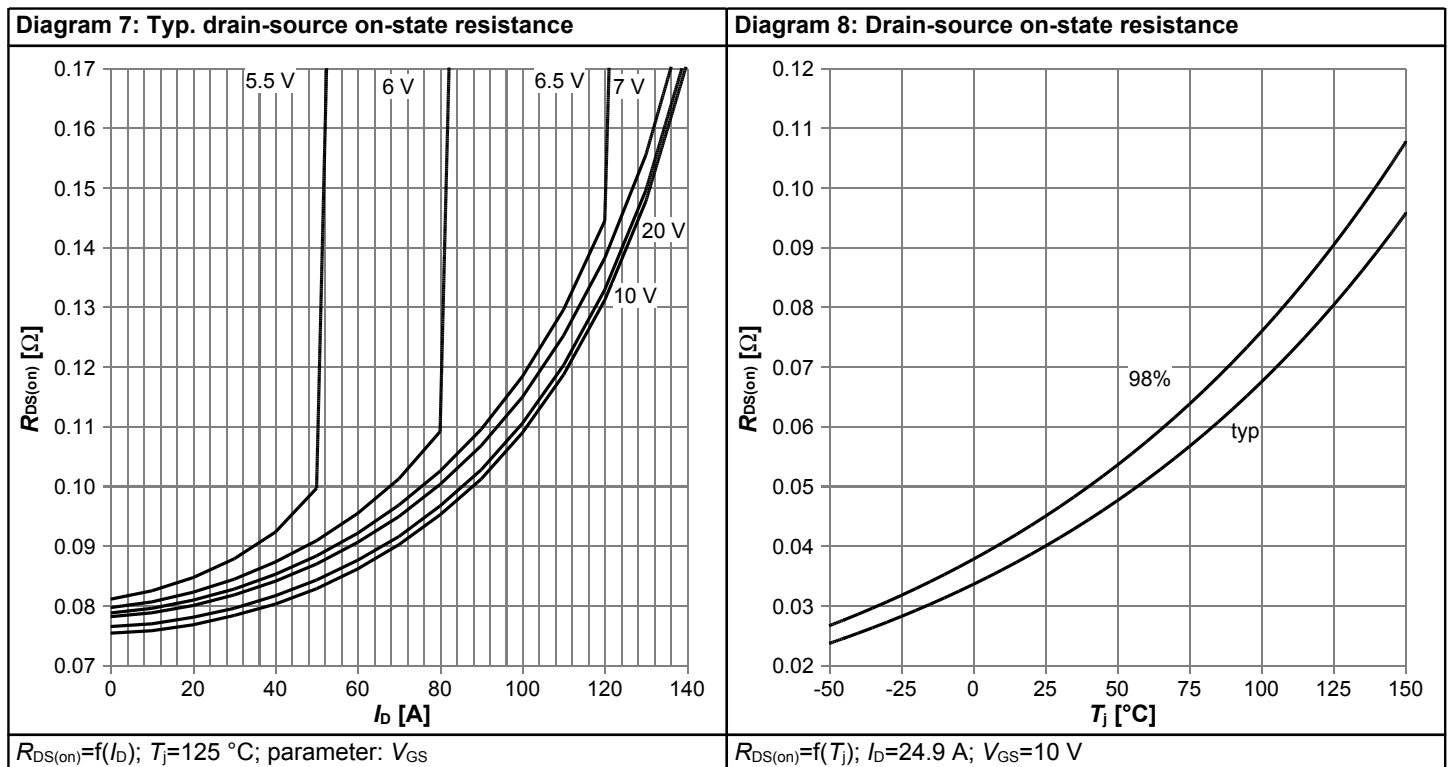


Table 12

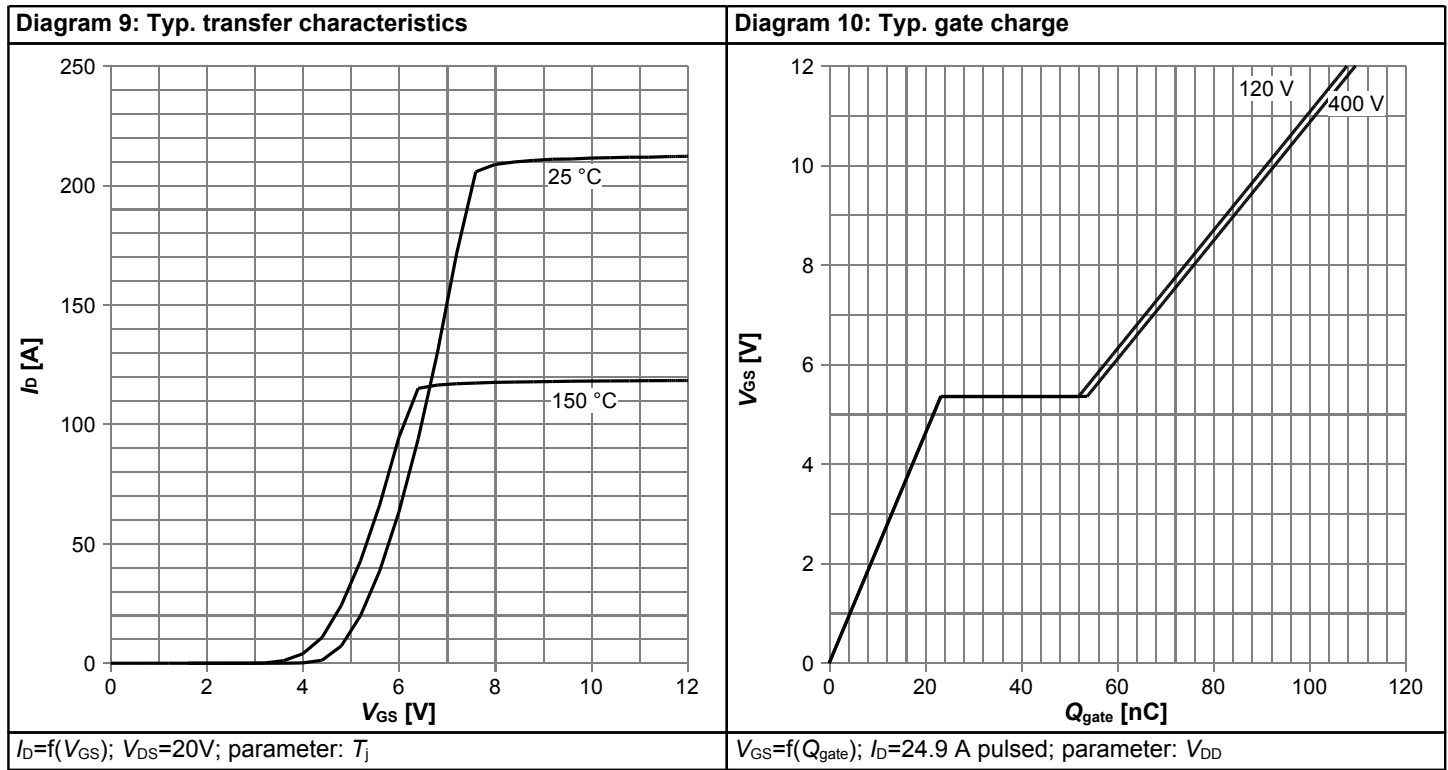


Table 13

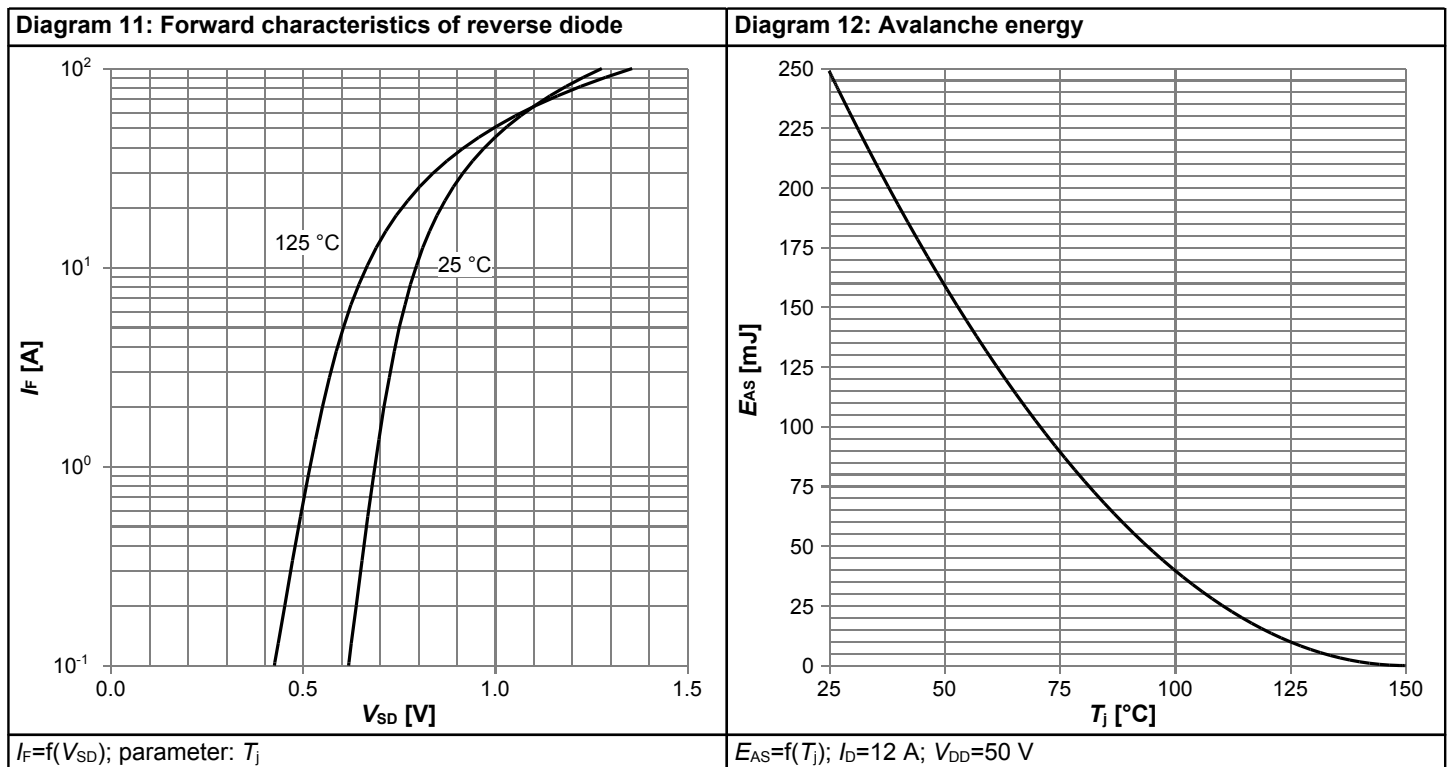


Table 14

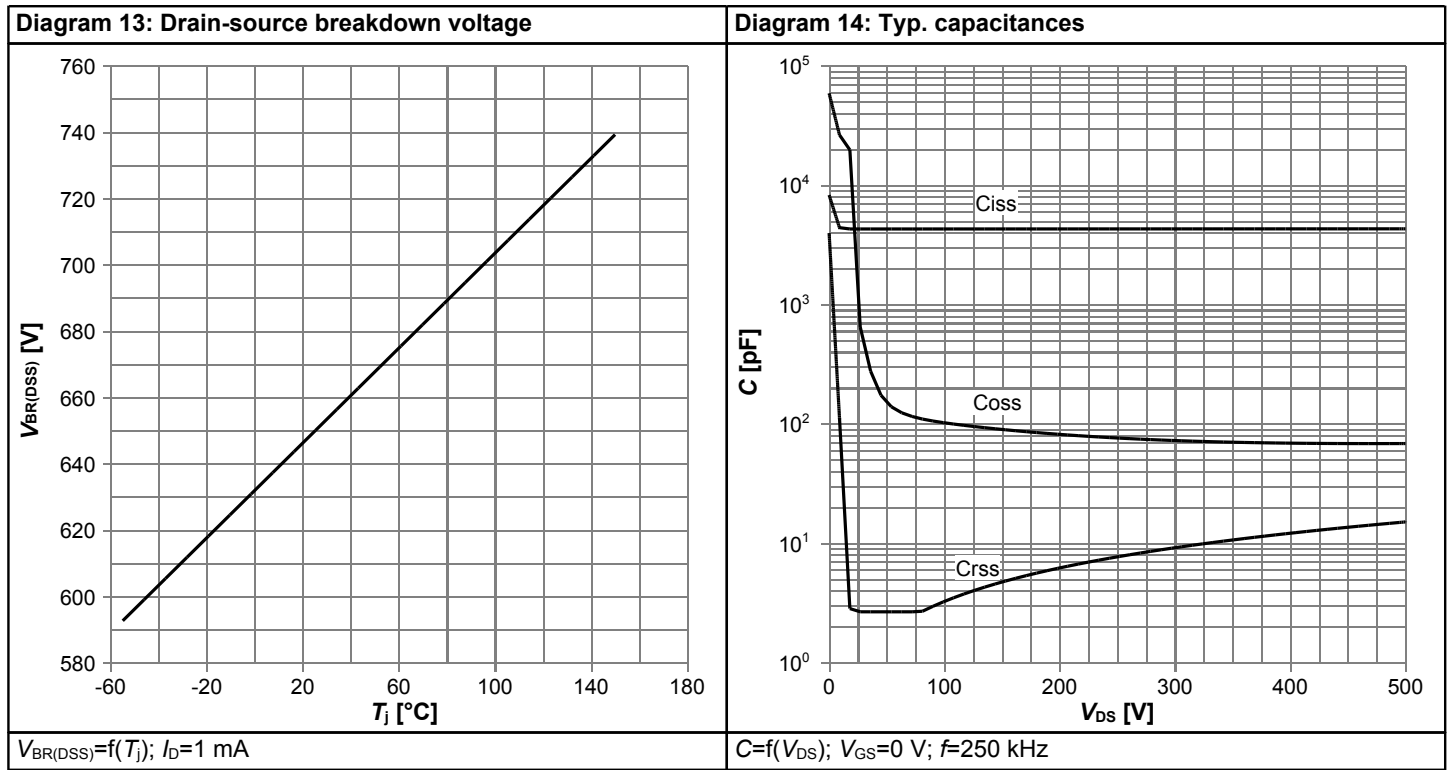
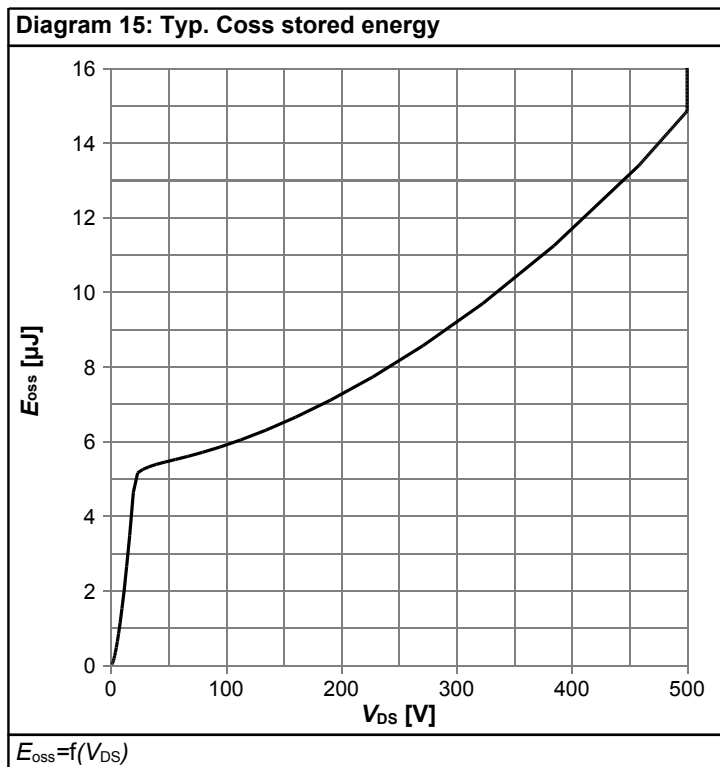


Table 15



6 Test Circuits

Table 16 Diode characteristics

Test circuit for diode characteristics	Diode recovery waveform
<p>$R_{g1} = R_{g2}$</p>	<p> $t_{tr} = t_F + t_s$ $Q_r = Q_F + Q_s$ </p>

Table 17 Switching times

Switching times test circuit for inductive load	Switching times waveform

Table 18 Unclamped inductive load

Unclamped inductive load test circuit	Unclamped inductive waveform

7 Package Outlines

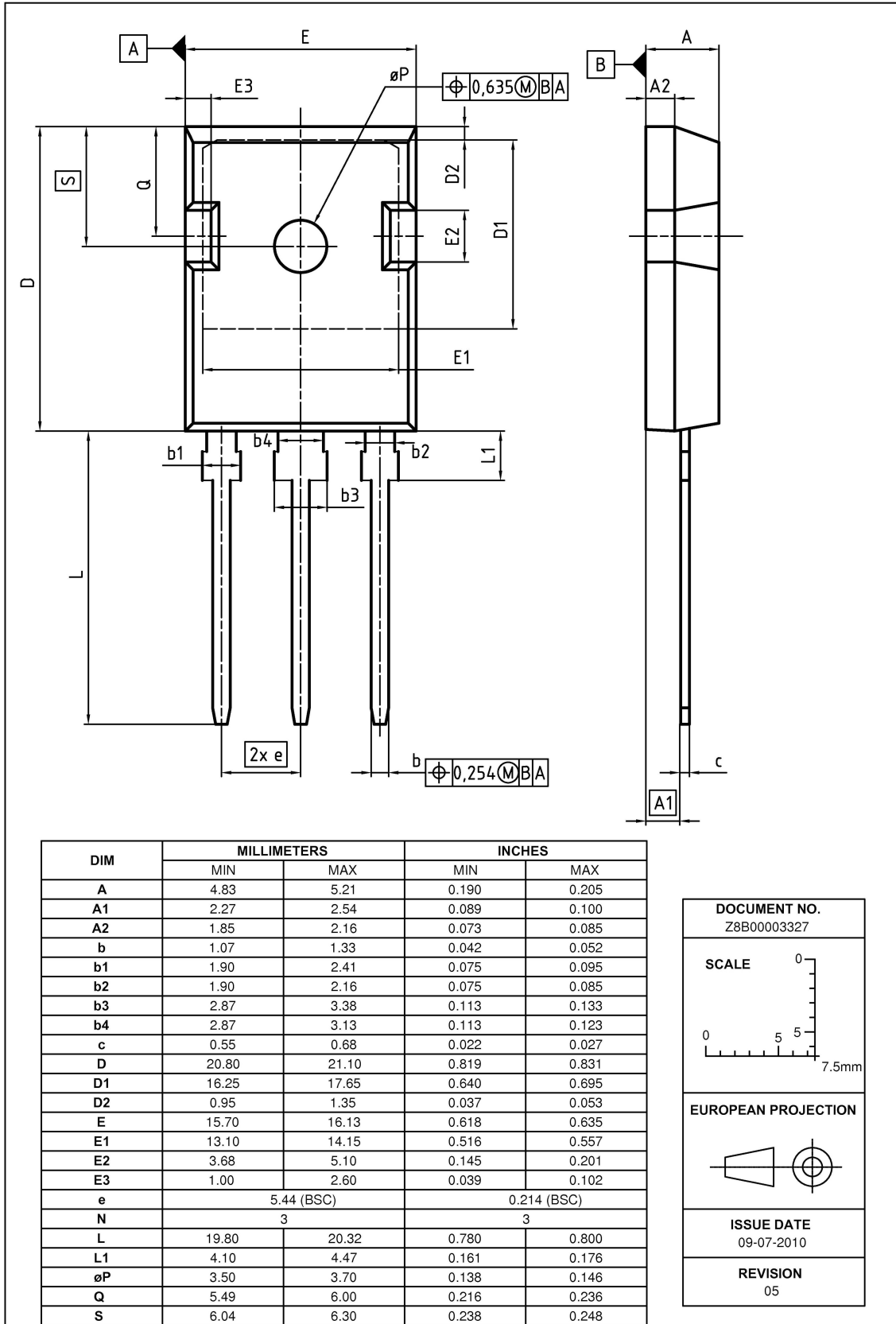


Figure 1 Outline PG-TO 247, dimensions in mm/inches

8 Appendix A

Table 19 Related Links

- IFX CoolMOS™ C7 Webpage: www.infineon.com
- IFX CoolMOS™ C7 application note: www.infineon.com
- IFX CoolMOS™ C7 simulation model: www.infineon.com
- IFX Design tools: www.infineon.com

Revision History

IPW65R045C7

Revision: 2013-04-30, Rev. 2.1

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.0	2013-04-18	Release of final version
2.1	2013-04-30	Body diode di/dt update

We Listen to Your Comments

Any information within this document that you feel is wrong, unclear or missing at all? Your feedback will help us to continuously improve the quality of this document. Please send your proposal (including a reference to this document) to:

erratum@infineon.com

Edition 2011-08-01**Published by****Infineon Technologies AG****81726 München, Germany****© 2011 Infineon Technologies AG****All Rights Reserved.**

Legal Disclaimer

The information given in this document shall in no event be regarded as a guarantee of conditions or characteristics. With respect to any examples or hints given herein, any typical values stated herein and/or any information regarding the application of the device, Infineon Technologies hereby disclaims any and all warranties and liabilities of any kind, including without limitation, warranties of non-infringement of intellectual property rights of any third party.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office (www.infineon.com).

Warnings

Due to technical requirements, components may contain dangerous substances. For information on the types in question, please contact the nearest Infineon Technologies Office.

The Infineon Technologies component described in this Data Sheet may be used in life-support devices or systems and/or automotive, aviation and aerospace applications or systems only with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support, automotive, aviation and aerospace device or system or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.